

Low Noise Dual/Quad Operational Amplifiers

MC33078, MC33079, NCV33078, NCV33079

The MC33078/9 series is a family of high quality monolithic amplifiers employing Bipolar technology with innovative high performance concepts for quality audio and data signal processing applications. This family incorporates the use of high frequency PNP input transistors to produce amplifiers exhibiting low input voltage noise with high gain bandwidth product and slew rate. The all NPN output stage exhibits no deadband crossover distortion, large output voltage swing, excellent phase and gain margins, low open loop high frequency output impedance and symmetrical source and sink AC frequency performance.

The MC33078/9 family offers both dual and quad amplifier versions and is available in the plastic DIP and SOIC packages (P and D suffixes).

Features

- Dual Supply Operation: ± 5.0 V to ± 18 V
- Low Voltage Noise: $4.5 \text{ nV}/\sqrt{\text{Hz}}$
- Low Input Offset Voltage: 0.15 mV
- Low T.C. of Input Offset Voltage: $2.0 \mu\text{V}/^\circ\text{C}$
- Low Total Harmonic Distortion: 0.002%
- High Gain Bandwidth Product: 16 MHz
- High Slew Rate: $7.0 \text{ V}/\mu\text{s}$
- High Open Loop AC Gain: $800 @ 20 \text{ kHz}$
- Excellent Frequency Stability
- Large Output Voltage Swing: $+14.1 \text{ V} / -14.6 \text{ V}$
- ESD Diodes Provided on the Inputs
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

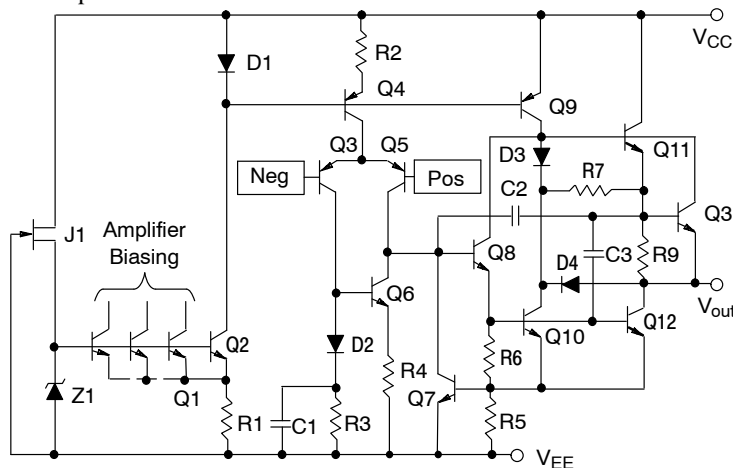
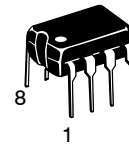


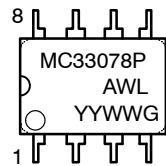
Figure 1. Representative Schematic Diagram
(Each Amplifier)

DUAL

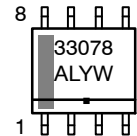


PDIP-8
P SUFFIX
CASE 626

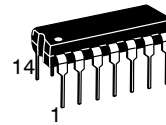
MARKING DIAGRAMS



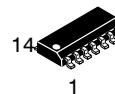
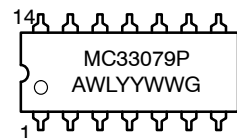
SOIC-8
D SUFFIX
CASE 751



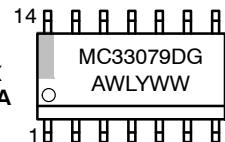
QUAD



PDIP-14
P SUFFIX
CASE 646



SOIC-14
D SUFFIX
CASE 751A



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or ■ = Pb-Free Package

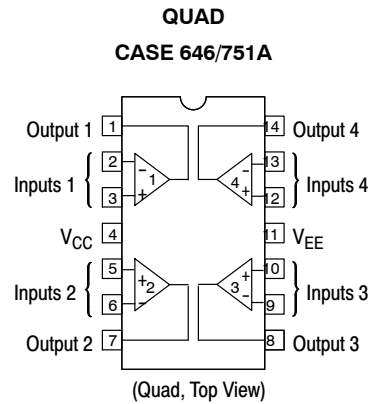
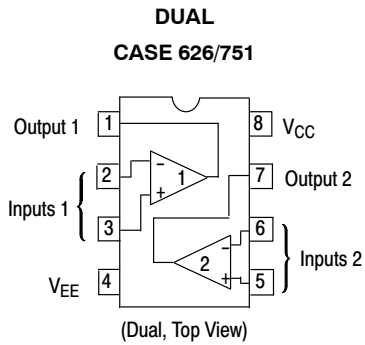
ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 10.

MC33078, MC33079, NCV33078, NCV33079

PIN CONNECTIONS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage (V_{CC} to V_{EE})	V_S	+36	V
Input Differential Voltage Range	V_{IDR}	Note 1	V
Input Voltage Range	V_{IR}	Note 1	V
Output Short Circuit Duration (Note 2)	t_{SC}	Indefinite	sec
Maximum Junction Temperature	T_J	+150	°C
Storage Temperature	T_{stg}	-60 to +150	°C
ESD Protection at any Pin MC33078/NCV33078 MC33079/NCV33079	V_{esd}	600 200 550 150	V
Maximum Power Dissipation	P_D	Note 2	mW
Operating Temperature Range	T_A	-40 to +85	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Either or both input voltages must not exceed the magnitude of V_{CC} or V_{EE} .

2. Power dissipation must be considered to ensure maximum junction temperature (T_J) is not exceeded (see Figure 2).

MC33078, MC33079, NCV33078, NCV33079

DC ELECTRICAL CHARACTERISTICS ($V_{CC} = +15\text{ V}$, $V_{EE} = -15\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted.)

Characteristics	Symbol	Min	Typ	Max	Unit
Input Offset Voltage ($R_S = 10\text{ }\Omega$, $V_{CM} = 0\text{ V}$, $V_O = 0\text{ V}$) (MC33078) $T_A = +25\text{ }^{\circ}\text{C}$ $T_A = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ (MC33079) $T_A = +25\text{ }^{\circ}\text{C}$ $T_A = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$	$ V_{IO} $	– – – –	0.15 – 0.15 –	2.0 3.0 2.5 3.5	mV
Average Temperature Coefficient of Input Offset Voltage $R_S = 10\text{ }\Omega$, $V_{CM} = 0\text{ V}$, $V_O = 0\text{ V}$, $T_A = T_{low}$ to T_{high}	$\Delta V_{IO}/\Delta T$	–	2.0	–	$\mu\text{V}/^{\circ}\text{C}$
Input Bias Current ($V_{CM} = 0\text{ V}$, $V_O = 0\text{ V}$) $T_A = +25\text{ }^{\circ}\text{C}$ $T_A = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$	I_{IB}	– –	300 –	750 800	nA
Input Offset Current ($V_{CM} = 0\text{ V}$, $V_O = 0\text{ V}$) $T_A = +25\text{ }^{\circ}\text{C}$ $T_A = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$	I_{IO}	– –	25 –	150 175	nA
Common Mode Input Voltage Range ($\Delta V_{IO} = 5.0\text{ mV}$, $V_O = 0\text{ V}$)	V_{ICR}	± 13	± 14	–	V
Large Signal Voltage Gain ($V_O = \pm 10\text{ V}$, $R_L = 2.0\text{ k}\Omega$) $T_A = +25\text{ }^{\circ}\text{C}$ $T_A = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$	A_{VOL}	90 85	110 –	– –	dB
Output Voltage Swing ($V_{ID} = \pm 1.0\text{ V}$) $R_L = 600\text{ }\Omega$ $R_L = 600\text{ }\Omega$ $R_L = 2.0\text{ k}\Omega$ $R_L = 2.0\text{ k}\Omega$ $R_L = 10\text{ k}\Omega$ $R_L = 10\text{ k}\Omega$	V_{O+} V_{O-} V_{O+} V_{O-} V_{O+} V_{O-}	– – $+13.2$ – $+13.5$ –	$+10.7$ -11.9 $+13.8$ -13.7 $+14.1$ -14.6	– – – -13.2 – -14	V
Common Mode Rejection ($V_{in} = \pm 13\text{ V}$)	CMR	80	100	–	dB
Power Supply Rejection (Note 3) $V_{CC}/V_{EE} = +15\text{ V}/-15\text{ V}$ to $+5.0\text{ V}/-5.0\text{ V}$	PSR	80	105	–	dB
Output Short Circuit Current ($V_{ID} = 1.0\text{ V}$, Output to Ground) Source Sink	I_{SC}	$+15$ -20	$+29$ -37	– –	mA
Power Supply Current ($V_O = 0\text{ V}$, All Amplifiers) (MC33078) $T_A = +25\text{ }^{\circ}\text{C}$ $T_A = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ (MC33079) $T_A = +25\text{ }^{\circ}\text{C}$ $T_A = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$	I_D	– – – –	4.1 – 8.4 –	5.0 5.5 10 11	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Measured with V_{CC} and V_{EE} differentially varied simultaneously.



MC33078, MC33079, NCV33078, NCV33079

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = +15\text{ V}$, $V_{EE} = -15\text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise noted.)

Characteristics	Symbol	Min	Typ	Max	Unit
Slew Rate ($V_{in} = -10\text{ V}$ to $+10\text{ V}$, $R_L = 2.0\text{ k}\Omega$, $C_L = 100\text{ pF}$, $A_V = +1.0$)	SR	5.0	7.0	–	V/ μs
Gain Bandwidth Product ($f = 100\text{ kHz}$)	GBW	10	16	–	MHz
Unity Gain Bandwidth (Open Loop)	BW	–	9.0	–	MHz
Gain Margin ($R_L = 2.0\text{ k}\Omega$ $C_L = 0\text{ pF}$ $C_L = 100\text{ pF}$)	A_m	– –	–11 –6.0	– –	dB
Phase Margin ($R_L = 2.0\text{ k}\Omega$ $C_L = 0\text{ pF}$ $C_L = 100\text{ pF}$)	ϕ_m	– –	55 40	– –	Deg
Channel Separation ($f = 20\text{ Hz}$ to 20 kHz)	CS	–	–120	–	dB
Power Bandwidth ($V_O = 27\text{ V}_{pp}$, $R_L = 2.0\text{ k}\Omega$, THD $\pm 1.0\%$)	BW_p	–	120	–	kHz
Total Harmonic Distortion ($R_L = 2.0\text{ k}\Omega$, $f = 20\text{ Hz}$ to 20 kHz , $V_O = 3.0\text{ V}_{rms}$, $A_V = +1.0$)	THD	–	0.002	–	%
Open Loop Output Impedance ($V_O = 0\text{ V}$, $f = 9.0\text{ MHz}$)	$ Z_O $	–	37	–	Ω
Differential Input Resistance ($V_{CM} = 0\text{ V}$)	R_{in}	–	175	–	$\text{k}\Omega$
Differential Input Capacitance ($V_{CM} = 0\text{ V}$)	C_{in}	–	12	–	pF
Equivalent Input Noise Voltage ($R_S = 100\text{ }\Omega$, $f = 1.0\text{ kHz}$)	e_n	–	4.5	–	$\text{nV}/\sqrt{\text{Hz}}$
Equivalent Input Noise Current ($f = 1.0\text{ kHz}$)	i_n	–	0.5	–	$\text{Hz}\sqrt{\text{pA}}$

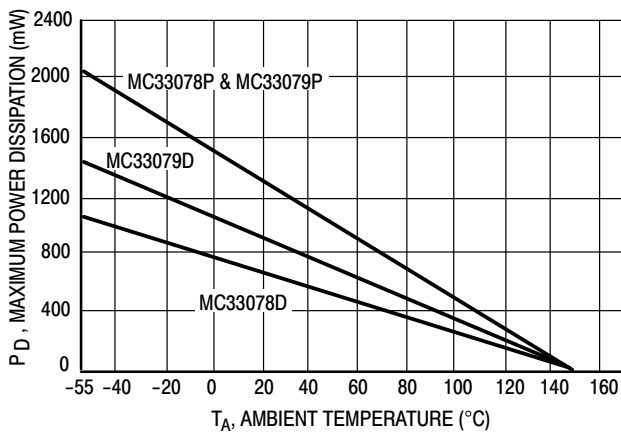


Figure 2. Maximum Power Dissipation versus Temperature

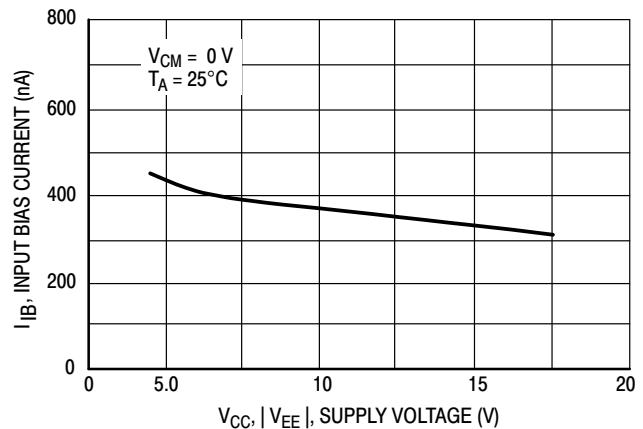


Figure 3. Input Bias Current versus Supply Voltage

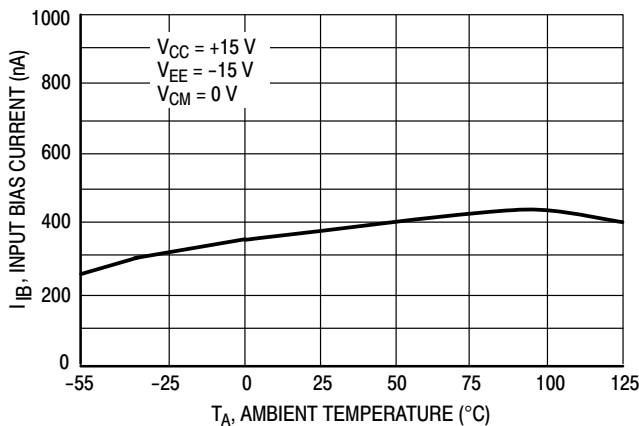


Figure 4. Input Bias Current versus Temperature

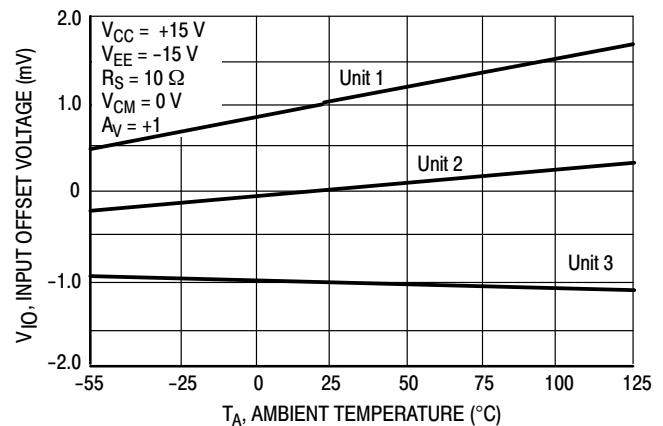


Figure 5. Input Offset Voltage versus Temperature

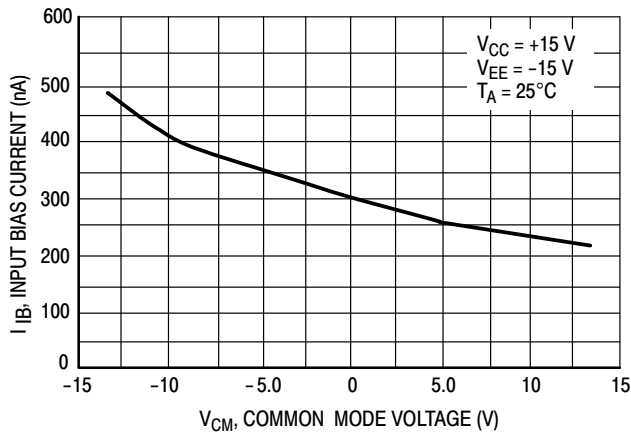


Figure 6. Input Bias Current versus Common Mode Voltage

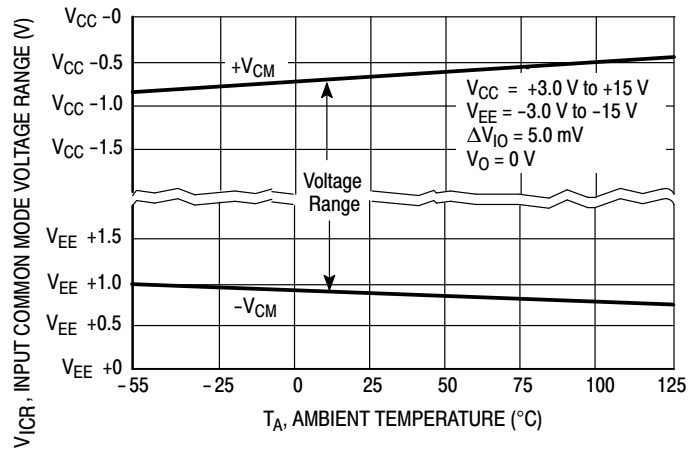


Figure 7. Input Common Mode Voltage Range versus Temperature

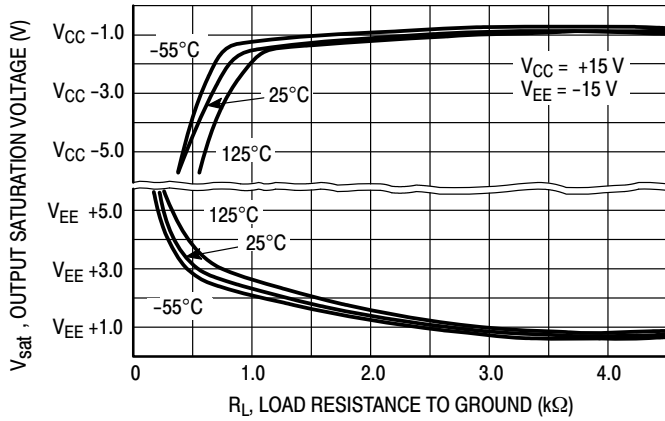


Figure 8. Output Saturation Voltage versus Load Resistance to Ground

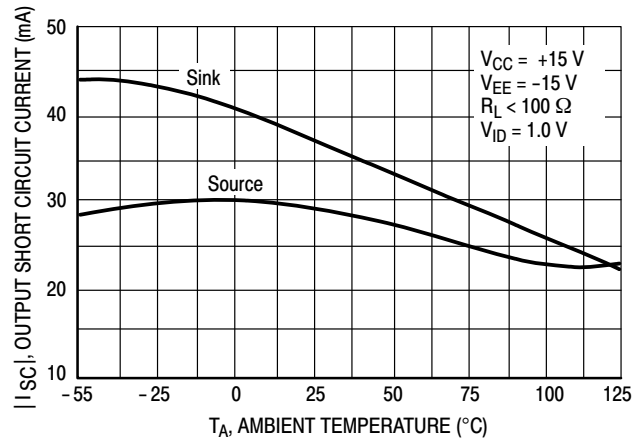


Figure 9. Output Short Circuit Current versus Temperature

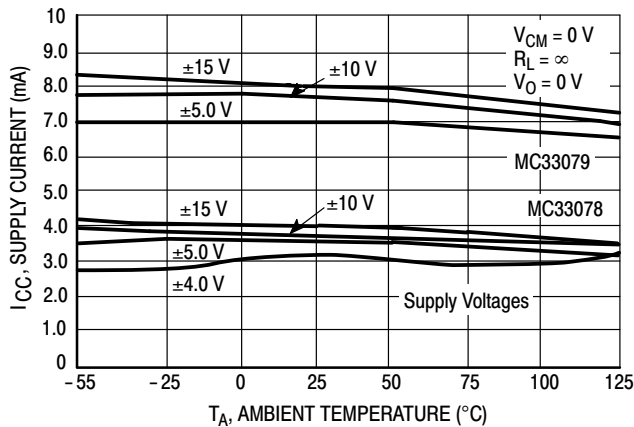


Figure 10. Supply Current versus Temperature

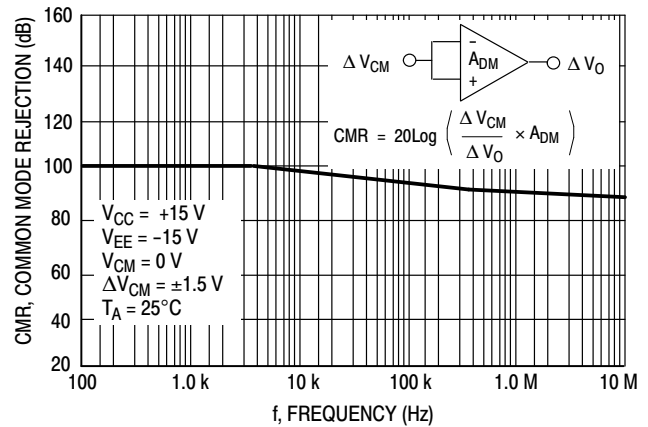


Figure 11. Common Mode Rejection versus Frequency

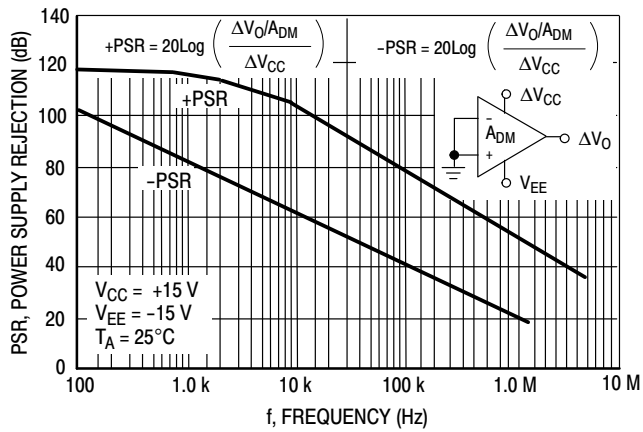


Figure 12. Power Supply Rejection versus Frequency

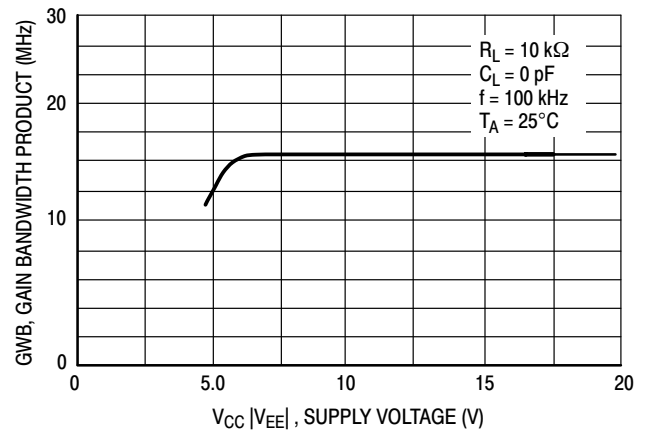


Figure 13. Gain Bandwidth Product versus Supply Voltage

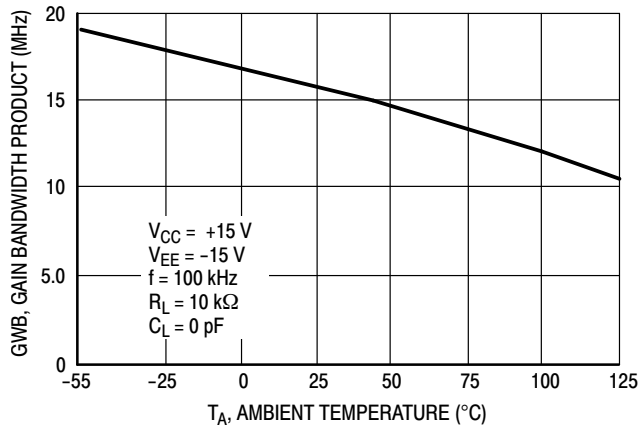


Figure 14. Gain Bandwidth Product versus Temperature

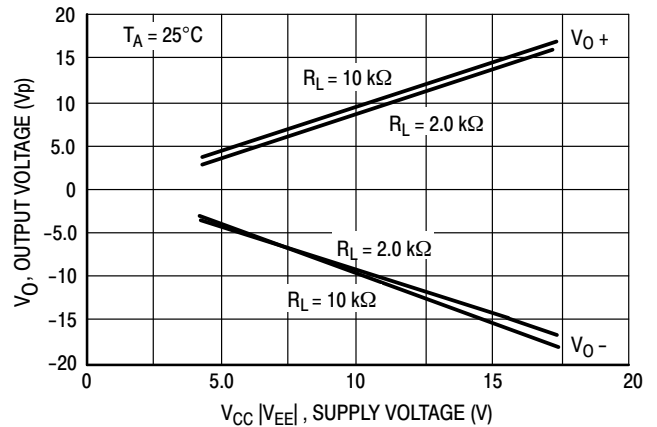


Figure 15. Maximum Output Voltage versus Supply Voltage

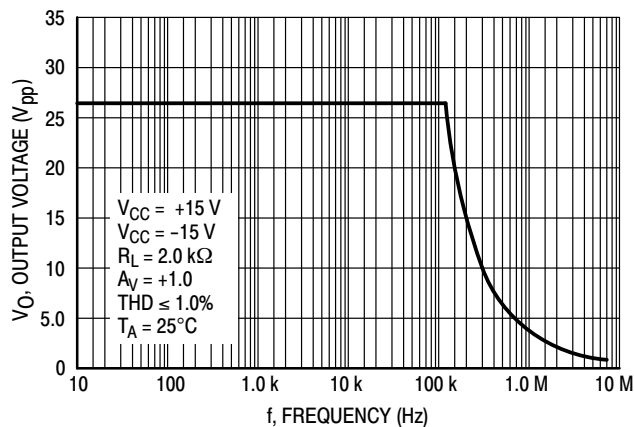


Figure 16. Output Voltage versus Frequency

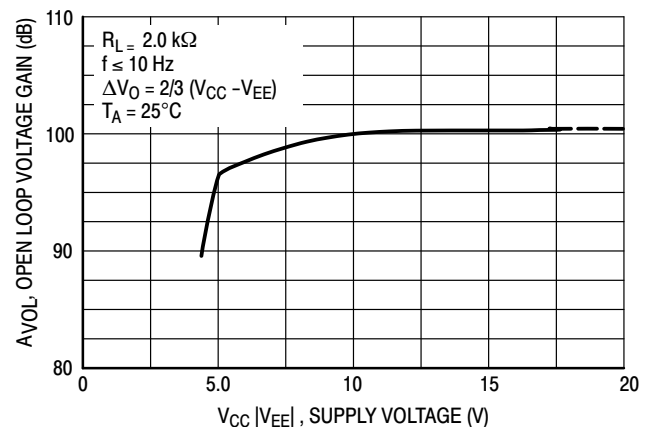


Figure 17. Open Loop Voltage Gain versus Supply Voltage

MC33078, MC33079, NCV33078, NCV33079

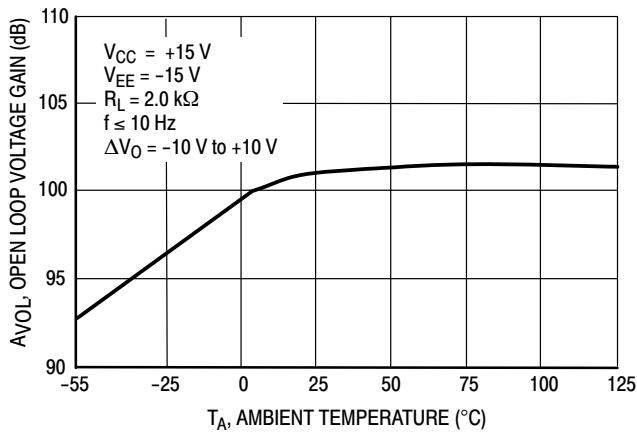


Figure 18. Open Loop Voltage Gain versus Temperature

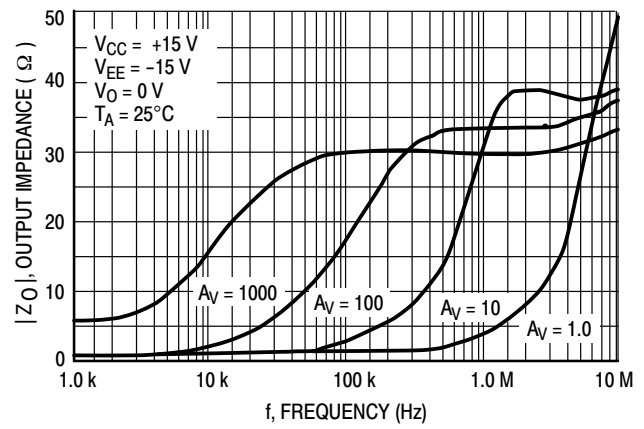


Figure 19. Output Impedance versus Frequency

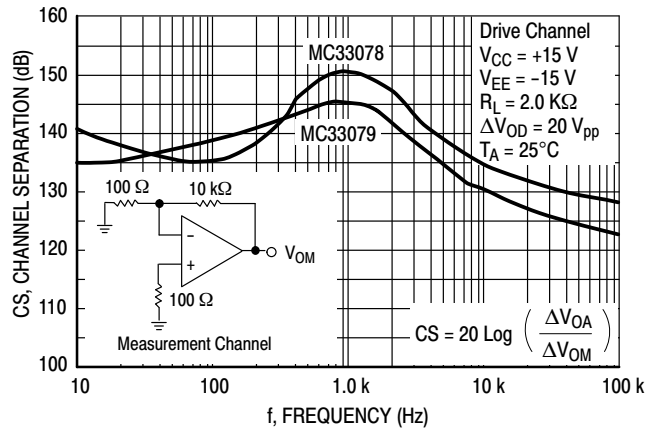


Figure 20. Channel Separation versus Frequency

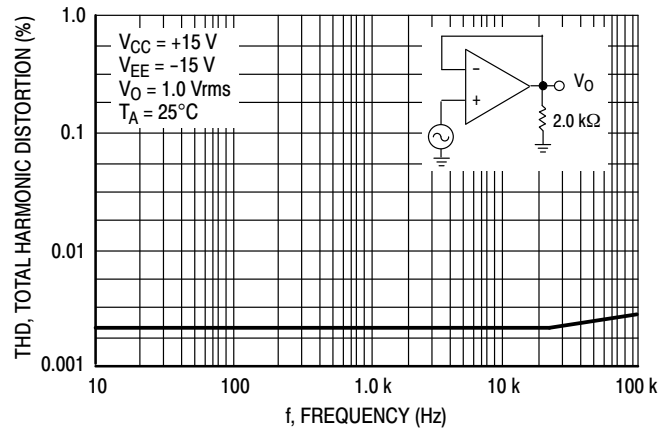


Figure 21. Total Harmonic Distortion versus Frequency

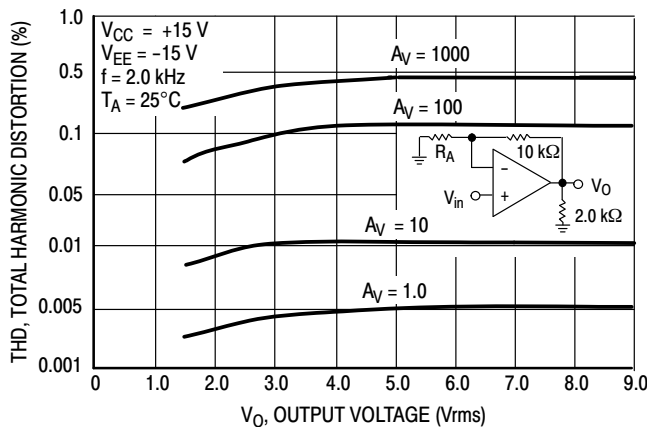


Figure 22. Total Harmonic Distortion versus Output Voltage

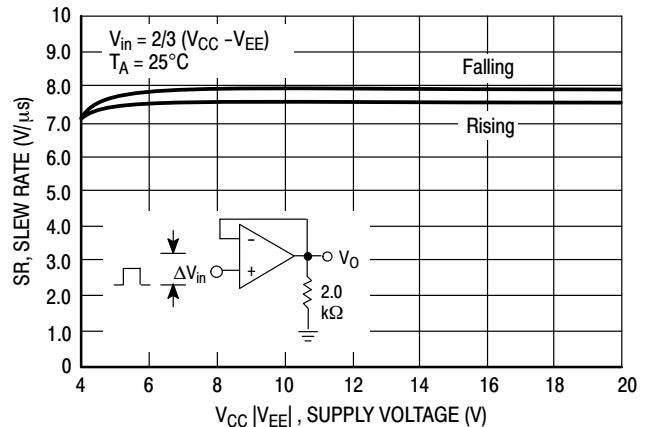


Figure 23. Slew Rate versus Supply Voltage

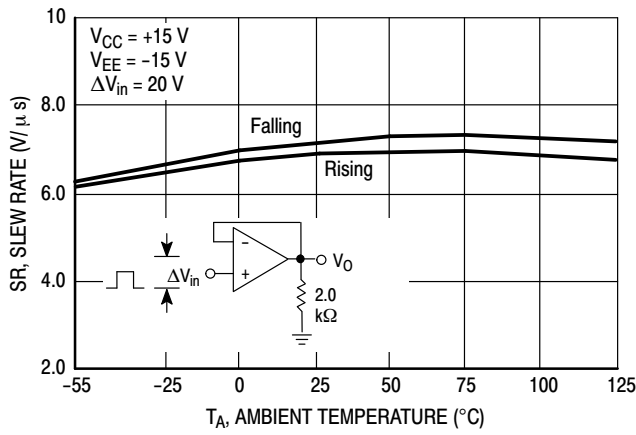


Figure 24. Slew Rate versus Temperature

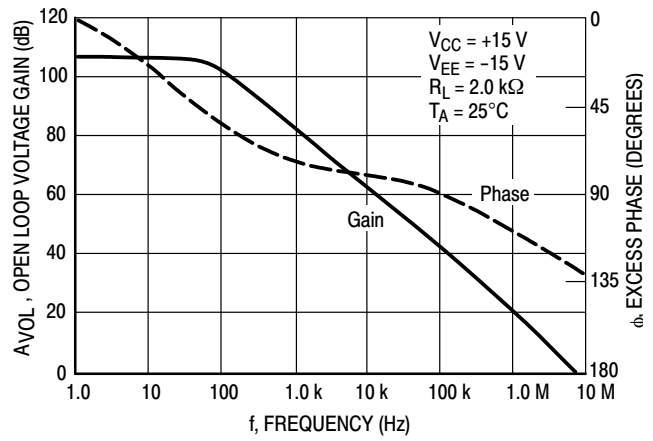


Figure 25. Voltage Gain and Phase versus Frequency

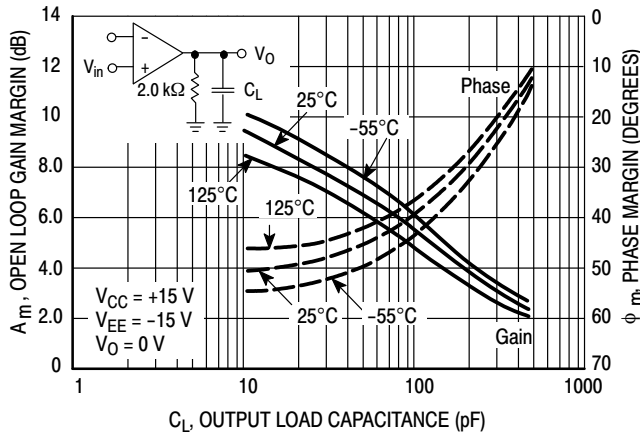


Figure 26. Open Loop Gain Margin and Phase Margin versus Load Capacitance

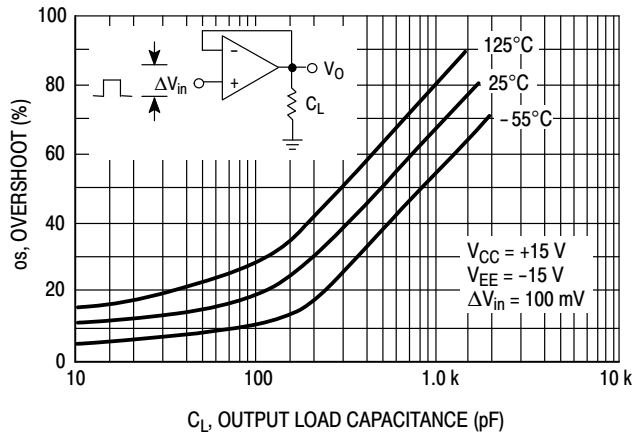


Figure 27. Overshoot versus Output Load Capacitance

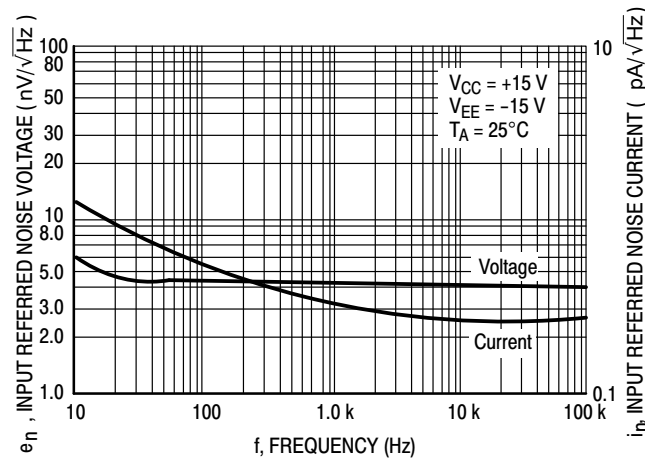


Figure 28. Input Referred Noise Voltage and Current versus Frequency

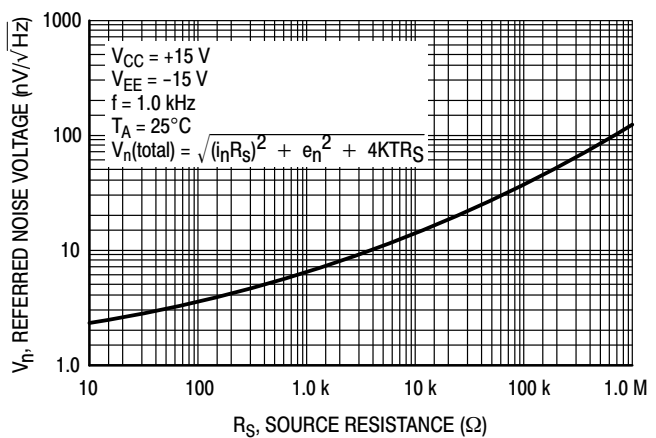


Figure 29. Total Input Referred Noise Voltage versus Source Resistance

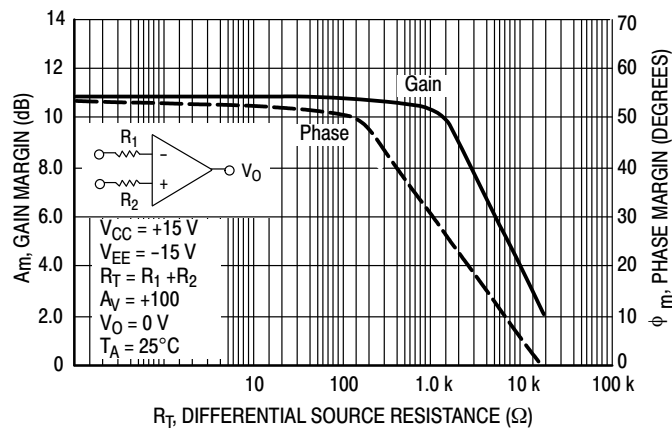


Figure 30. Phase Margin and Gain Margin versus Differential Source Resistance

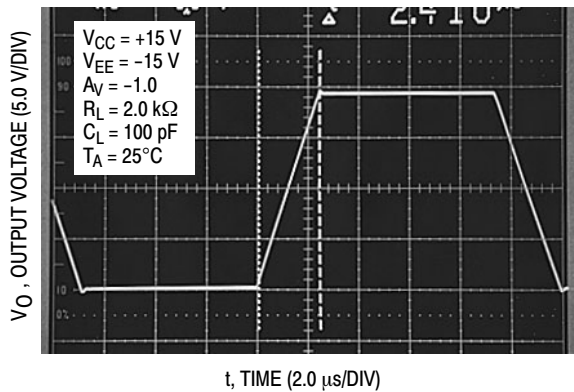


Figure 31. Inverting Amplifier Slew Rate

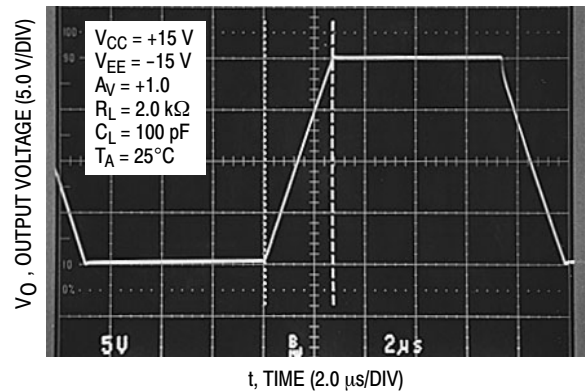


Figure 32. Non-inverting Amplifier Slew Rate

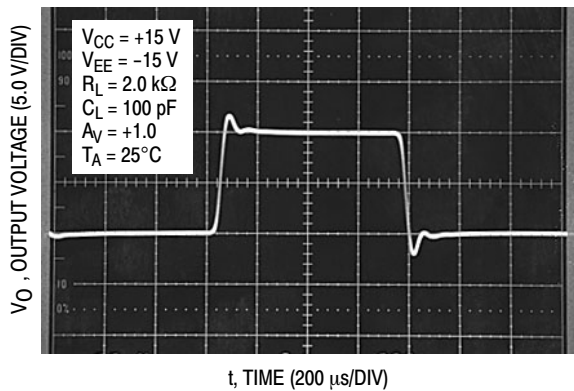


Figure 33. Non-inverting Amplifier Overshoot

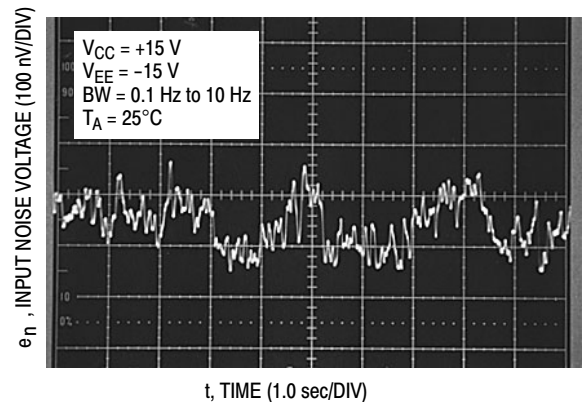
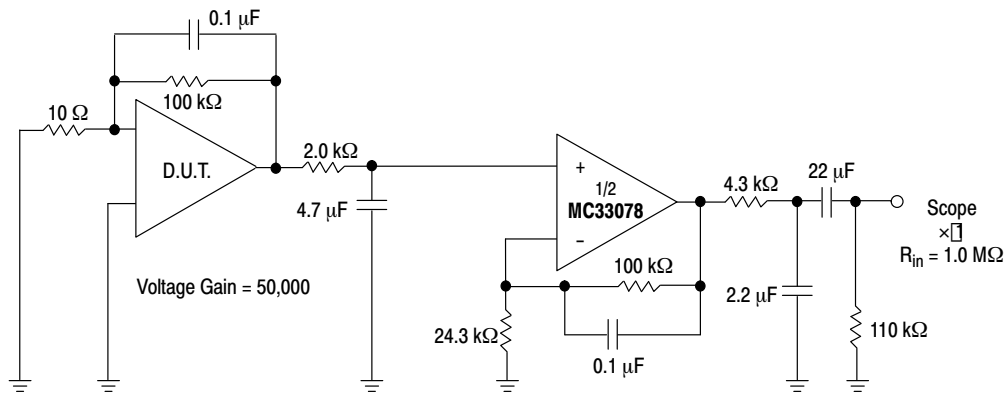


Figure 34. Low Frequency Noise Voltage versus Time

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Note: All capacitors are non-polarized.

Figure 35. Voltage Noise Test Circuit
(0.1 Hz to 10 Hz_{p-p})

ORDERING INFORMATION

Device	Package	Shipping [†]
MC33078DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC33079DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
NCV33079DR2G*		

DISCONTINUED (Note 4)

MC33078DG	SOIC-8 (Pb-Free)	98 Units / Rail
NCV33078DR2G*	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC33078P	PDIP-8	50 Units / Rail
MC33078PG	PDIP-8 (Pb-Free)	50 Units / Rail
MC33079DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC33079P	PDIP-14	25 Units / Rail
MC33079PG	PDIP-14 (Pb-Free)	25 Units / Rail

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

* NCV devices are qualified for automotive use.

4. **DISCONTINUED:** These devices are not available. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

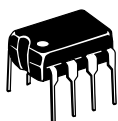
MC33078, MC33079, NCV33078, NCV33079

REVISION HISTORY

Revision	Description of Changes	Date
10	Rebranded the Data Sheet to onsemi format. MC33078DG, NCV33078DR2G, MC33078P, MC33078PG, MC33079DG, MC33079P, MC33079PG OPNs Marked as Discontinued.	07/30/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

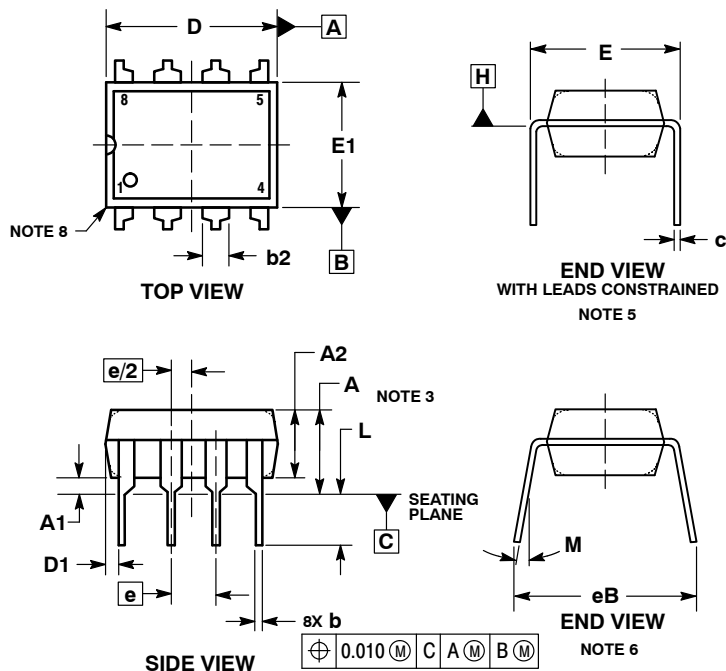




SCALE 1:1

PDIP-8
CASE 626-05
ISSUE P

DATE 22 APR 2015



STYLE 1:

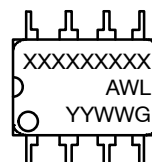
- PIN 1. AC IN
2. DC + IN
3. DC - IN
4. AC IN
5. GROUND
6. OUTPUT
7. AUXILIARY
8. V_{CC}

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.015	0.210	0.38	5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
C	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
M		10 ⁻³		10 ⁻³

GENERIC MARKING DIAGRAM*

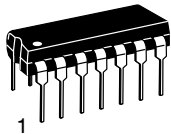


- XXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "μ", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	PDIP-8	PAGE 1 OF 1

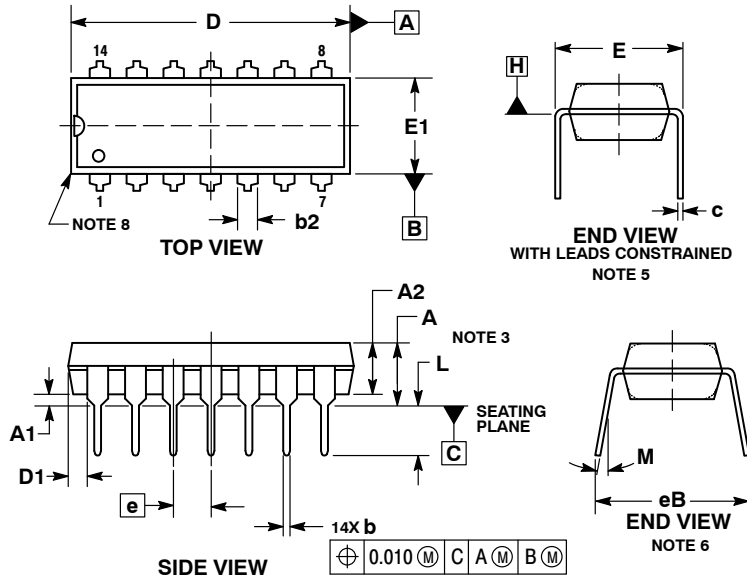
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SCALE 1:1

PDIP-14
CASE 646-06
ISSUE S

DATE 22 APR 2015

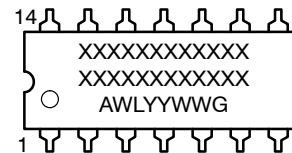


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	---	0.210	---	5.33
A1	0.015	---	0.38	---
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP 1.52 TYP			
C	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005	---	0.13	---
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
eB	---	0.430	---	10.92
L	0.115	0.150	2.92	3.81
M	---	10°	---	10°

GENERIC
MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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PDIP-14
CASE 646-06
ISSUE S

DATE 22 APR 2015

STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NO
CONNECTION
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NO
CONNECTION
12. EMITTER
13. BASE
14. COLLECTOR

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. NO
CONNECTION
5. GATE
6. SOURCE
7. DRAIN
8. DRAIN
9. SOURCE
10. GATE
11. NO
CONNECTION
12. GATE
13. SOURCE
14. DRAIN

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. NO CONNECTION
5. SOURCE
6. DRAIN
7. GATE
8. GATE
9. DRAIN
10. SOURCE
11. NO CONNECTION
12. SOURCE
13. DRAIN
14. GATE

STYLE 6:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 7:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON
CATHODE

STYLE 8:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 9:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

STYLE 10:
PIN 1. COMMON
CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON
CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 12:
PIN 1. COMMON CATHODE
2. COMMON ANODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. COMMON ANODE
7. COMMON CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. ANODE/CATHODE
14. ANODE/CATHODE

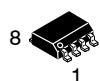
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DESCRIPTION: PDIP-14

PAGE 2 OF 2

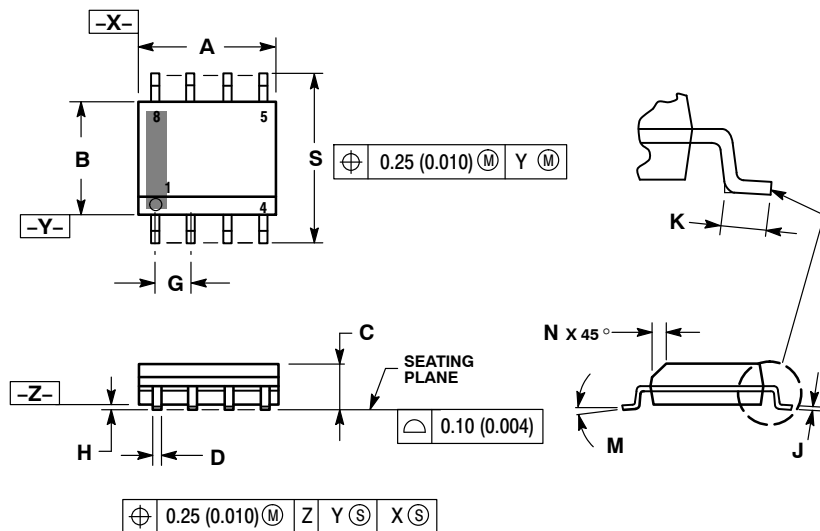
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SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

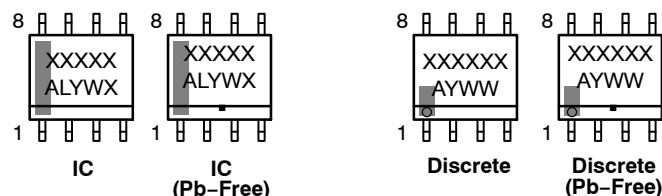
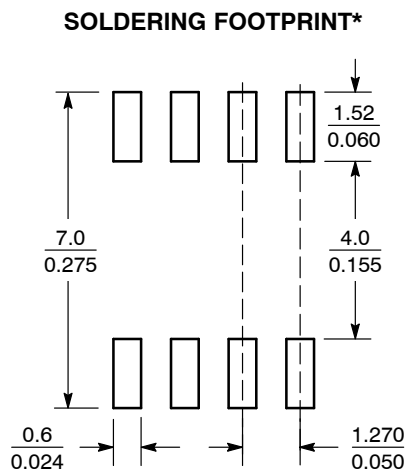


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC
MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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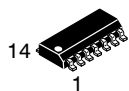
SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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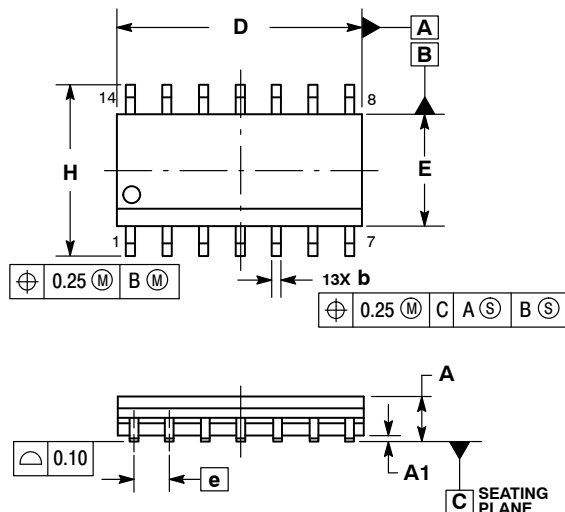
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SCALE 1:1

SOIC-14 NB
CASE 751A-03
ISSUE L

DATE 03 FEB 2016

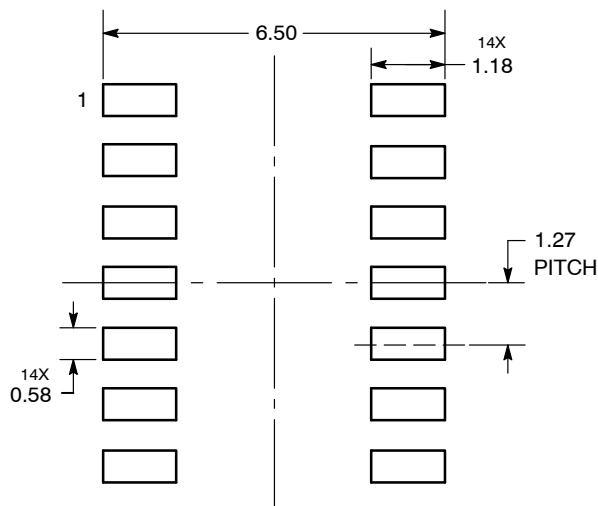


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

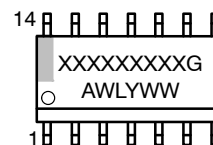
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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SOIC-14
CASE 751A-03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

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